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(71) Applicant *(for all designated States except US)*: **S.O.I.TEC SILICON ON INSULATOR TECHNOLOGIES** [FR/FR]; Parc Technologique des Fontaines, Chemin des Franques, F-38190 Bernin (FR).

(72) Inventor; and

(75) Inventor/Applicant *(for US only)*: **LANDRU, Didier** [FR/FR]; Rue des Armariniers, F-38190 Champ Pres Froges (FR).

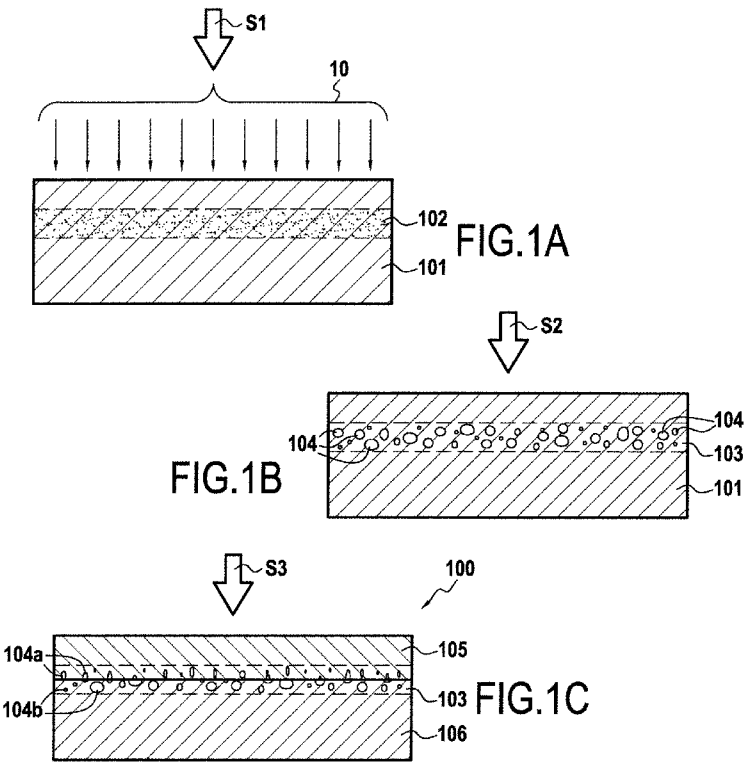
(74) Agents: **DESORMIERE, Pierre-Louis** et al.; Cabinet BEAU DE LOMENIE, 158 rue de l'Université, F-75340 Paris Cedex 07 (FR).

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(54) Title: A METHOD OF PRODUCING A LAYER OF CAVITIES.



(57) Abstract: A method of producing a layer of cavities in a structure (100) comprises at least one substrate (101) formed from a material that can be oxidized or nitrided, the method comprising the following steps: implanting ions (10) into said substrate (101) in order to form an implanted ion concentration zone (102) at a predetermined mean depth; heat treating the implanted substrate to form a layer of cavities (103) at the implanted ion concentration zone (102); and forming an insulating layer (105) in said substrate by thermochemical treatment from one surface of said substrate, said insulating layer that is formed extending at least partially into the layer of cavities (103).

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